

## By passing Reliable Multiplier Using Adaptive Hold Logic

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### ABSTRACT:

Digital multipliers are among the most critical arithmetic functional units. The overall performance of these systems depends on the throughput of the multiplier. Meanwhile, the negative bias temperature instability effect occurs when a pMOS transistor is under negative bias ( $V_{gs} = -V_{dd}$ ), increasing the threshold voltage of the pMOS transistor, and reducing multiplier speed. A similar phenomenon, positive bias temperature instability, occurs when an nMOS transistor is under positive bias. Both effects degrade transistor speed, and in the long term, the system may fail due to timing violations.

Therefore, it is important to design reliable high-performance multipliers. In this paper, we propose an aging-aware multiplier design with novel adaptive hold logic (AHL) circuit using booth multiplier algorithm. The multiplier is able to provide higher throughput through the variable latency and can adjust the AHL circuit to mitigate performance degradation that is due to the aging effect. Moreover, the proposed architecture can be applied to a column-row-bypassing multiplier.

### 1. INTRODUCTION:

Digital multipliers are among the most critical arithmetic functional units in many applications, such as the Fourier transform, discrete cosine transforms, and digital filtering. The throughput of these applications depends on multipliers, and if the multipliers are too slow, the performance of entire circuits will be reduced. Furthermore, negative bias temperature instability (NBTI) occurs when a pMOS transistor is under negative bias ( $V_{gs} = -V_{dd}$ ).

In this situation, the interaction between inversion layer holes and hydrogen-passivated Si atoms breaks the Si-H bond generated during the oxidation process, generating H or H<sub>2</sub> molecules. When these molecules diffuse away, interface traps are left.

The accumulated interface traps between silicon and the gate oxide interface result in increased threshold voltage ( $V_{th}$ ), reducing the circuit switching speed. When the biased voltage is removed, the reverse reaction occurs, reducing the NBTI effect. However, the reverse reaction does not eliminate all the interface traps generated during the stress phase, and  $V_{th}$  is increased in the long term. Hence, it is important to design a reliable high-performance multiplier. The corresponding effect on an nMOS transistor is positive bias temperature instability (PBTI), which occurs when an nMOS transistor is under positive bias. Compared with the NBTI effect, the PBTI effect is much smaller on oxide/polygate transistors, and therefore is usually ignored.

However, for high-k/metal-gate nMOS transistors with significant charge trapping, the PBTI effect cannot longer be ignored. In fact, it has been shown that the PBTI effect is more significant than the NBTI effect on 32-nm high-k/metal-gate processes. A traditional method to mitigate the aging effect is overdesign, including such things as guardbanding and gate oversizing; however, this approach can be very pessimistic and area and power inefficient. To avoid this problem, many NBTI-aware methodologies have been proposed. An NBTI-aware technology mapping technique was proposed in to guarantee the performance of the circuit during its lifetime.

In an NBTI-aware sleep transistor was designed to reduce the aging effects on pMOS sleep-transistors, and the lifetime stability of the power-gated circuits under consideration was improved. Wu and Marculescu proposed a point logic restructuring and pin reordering method, which is based on detecting functional symmetries and transistor stacking effects. They also proposed an NBTI optimization method that considered path sensitization. In dynamic voltage scaling and body-biasing techniques were proposed to reduce power or extend circuit life. These techniques, however, require circuit modification or do not provide optimization of specific circuits.

Traditional circuits use critical path delay as the overall circuit clock cycle in order to perform correctly. However, the probability that the critical paths are activated is low. In most cases, the path delay is shorter than the critical path. For these noncritical paths, using the critical path delay as the overall cycle period will result in significant timing waste. Hence, the variable-latency design was proposed to reduce the timing waste of traditional circuits. The variable-latency design divides the circuit into two parts: 1) shorter paths and 2) longer paths. Shorter paths can execute correctly in one cycle, whereas longer paths need two cycles to execute. When shorter paths are activated frequently, the average latency of variable-latency designs is better than that of traditional designs. For example, several variable-latency adders were proposed using the speculation technique with error detection and recovery. A short path activation function algorithm was proposed to improve the accuracy of the hold logic and to optimize the performance of the variable-latency circuit. An instruction scheduling algorithm was proposed to schedule the operations on non uniform latency functional units and improve the performance of Very Long Instruction Word processors. In a variable-latency pipelined multiplier architecture with a Booth algorithm was proposed. In process-variation tolerant architecture for arithmetic units was proposed, where the effect of process-variation is considered to increase the circuit yield. I

In addition, the critical paths are divided into two shorter paths that could be unequal and the clock cycle is set to the delay of the longer one. These research designs were able to reduce the timing waste of traditional circuits to improve performance, but they did not consider the aging effect and could not adjust themselves during the runtime. A variable-latency adder design that considers the aging effect was proposed. However, no variable-latency multiplier design that considers the aging effect and can adjust dynamically has been done.

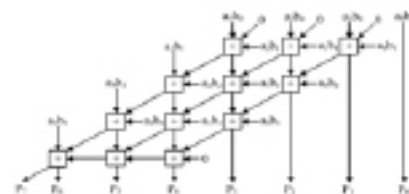
## II. PAPER CONTRIBUTION:

In this paper, we propose an aging-aware reliable multiplier design with novel adaptive hold logic (AHL) circuit. The multiplier is based on the variable-latency technique and can adjust the AHL circuit to achieve reliable operation under the influence of NBTI and PBTI effects.

To be specific, the contributions of this paper are summarized as follows: 1) novel variable-latency multiplier architecture with an AHL circuit. The AHL circuit can decide whether the input patterns require one or two cycles and can adjust the judging criteria to ensure that there is minimum performance degradation after considerable aging occurs; 2) comprehensive analysis and comparison of the multiplier's performance under different cycle periods to show the effectiveness of our proposed architecture; 3) an aging-aware reliable multiplier design method that is suitable for large multipliers. Although the experiment is performed in 16- and 32-bit multipliers, our proposed architecture can be easily extended to large designs; 4) the experimental results show that our proposed architecture with the  $16 \times 16$  and  $32 \times 32$  column-bypassing multipliers can attain up to 62.88% and 76.28% performance improvement compared with the  $16 \times 16$  and  $32 \times 32$  fixed-latency column-bypassing (FLCB) multipliers. In addition, our proposed architecture with  $16 \times 16$  and  $32 \times 32$  row-bypassing multipliers can achieve up to 80.17% and 69.40% performance improvement as compared with  $16 \times 16$  and  $32 \times 32$  fixed-latency row-bypassing multipliers.

## III. PRELIMINARIES: Row-Bypassing Multiplier:

A low-power row-bypassing multiplier [23] is also proposed to reduce the activity power of the AM. The operation of the low-power row-bypassing multiplier is similar to that of the low-power column-bypassing multiplier, but the selector of the multiplexers and the tristate gates use the multiplier.



**Figure 1 :  $4 \times 4$  Row-Bypassing Multiplier**

Fig. 3 is a  $4 \times 4$  row-bypassing multiplier. Each input is connected to an FA through a tristate gate. When the inputs are  $11112 * 10012$ , the two inputs in the first and second rows are 0 for FAs. Because  $b_1$  is 0, the multiplexers in the first row select  $aib_0$  as the sum bit and select 0 as the carry bit. The inputs are bypassed to FAs in the second rows, and the tristate gates turn off the input paths to the FAs.

Therefore, no switching activities occur in the first-row FAs; in return, power consumption is reduced. Similarly, because  $b_2$  is 0, no switching activities will occur in the second-row FAs. However, the FAs must be active in the third row because the  $b_3$  is not zero.

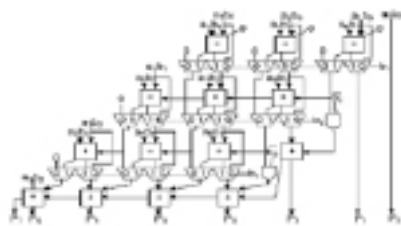


Figure 2 : 4 × 4 column-bypassing multiplier.

selector of the multiplexer to decide the output of the FA, and  $a_{can}$  also be used as the selector of the tristate gate to turn off the input path of the FA. If  $a_{can}$  is 0, the inputs of FA are disabled, and the sum bit of the current FA is equal to the sum bit from its upper FA, thus reducing the power consumption of the multiplier. If  $a_{can}$  is 1, the normal sum result is selected. More details for the column-bypassing multiplier can be found.

## IV. PROPOSED AGING-AWARE MULTIPLIER:

The proposed aging-aware reliable multiplier design. It introduces the overall architecture and the functions of each component and also describes how to design AHL that adjusts the circuit when significant aging occurs.

### Proposed Architecture:

Proposed aging-aware multiplier architecture, which includes two  $m$ -bit inputs ( $m$  is a positive number), one  $2m$ -bit output, one column- or row-bypassing multiplier,  $2m$  1-bit Razor flip-flops, and an AHL circuit.

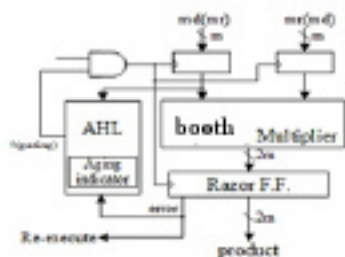


Figure 3: Proposed architecture (md means multiplicand; mr means multiplier).

Razor flip-flops can be used to detect whether timing violations occur before the next input pattern arrives. A 1-bit Razor flip-flop contains a main flip-flop, shadow latch, XOR gate, and mux. The main flip-flop catches the execution result for the combination circuit using a normal clock signal, and the shadow latch catches the execution result using a delayed clock signal, which is slower than the normal clock signal. If the latched bit of the shadow latch is different from that of the main flip-flop, this means the path delay of the current operation exceeds the cycle period, and the main flip-flop catches an incorrect result. If errors occur, the Razor flip-flop will set the error signal to 1 to notify the system to reexecute the operation and notify the AHL circuit that an error has occurred. We use Razor flip-flops to detect whether an operation that is considered to be a one-cycle pattern can really finish in a cycle. If not, the operation is reexecuted with two cycles. Although the reexecution may seem costly, the overall cost is low because the reexecution frequency is low.

More details for the Razor flip-flop can be found. The AHL circuit is the key component in the aging-aware variable-latency multiplier. Fig. shows the details of the AHL circuit. The AHL circuit contains an aging indicator, two judging blocks, one mux, and one D flip-flop. The aging indicator indicates whether the circuit has suffered significant performance degradation due to the aging effect. The aging indicator is implemented in a simple counter that counts the number of errors over a certain amount of operations and is reset to zero at the end of those operations. If the cycle period is too short, the column- or row-bypassing multiplier is not able to complete these operations successfully, causing timing violations.



Figure 4 : Razor flip flops.

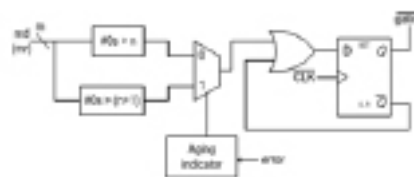


Figure 5: Diagram of AHL (md means multiplicand; mr means multiplier).





### Area & Delay Reports:

Device Utilization Summary (estimated values)			
Logic Utilization	Used	Available	Utilization
Number of Slice LUTs	22	9112	0%
Number of fully used LUT-FF pairs	0	22	0%
Number of bonded IOBs	16	232	6%

a)

Timing Summary:  
-----  
Speed Grade: -2

Minimum period: No path found  
Minimum input arrival time before clock: No path found  
Maximum output required time after clock: No path found  
Maximum combinational path delay: 10.725ns

b)

Figure 6: a) Area & b) Delay for Existing

Device Utilization Summary (estimated values)			
Logic Utilization	Used	Available	Utilization
Number of Slice Registers	44	18224	0%
Number of Slice LUTs	67	9112	0%
Number of fully used LUT-FF pairs	18	93	19%
Number of bonded IOBs	21	232	9%
Number of BUFG, BUFGCTRLs	3	16	18%

a)

Timing Summary:  
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Speed Grade: -2

Minimum period: 5.392ns (Maximum Frequency: 185.460MHz)  
Minimum input arrival time before clock: 5.518ns  
Maximum output required time after clock: 6.949ns  
Maximum combinational path delay: No path found

b)

Figure 7: a)Area & b) Delay for Proposed

### VI.CONCLUSION:

This paper proposed an aging-aware variable-latency multiplier design with the AHL. The multiplier is able to adjust the AHL to mitigate performance degradation due to increased delay. The experimental results show that our proposed architecture with 4x4 multiplication with Booth as last stage instead of Normal RCA adder it will decrease the delay and improve the performance compared with previous designs.

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